SD1490-1

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1490-1** is a Common Emitter Device Designed for Class A and AB Amplifier Applications in Television Band IV & V Transmitters.

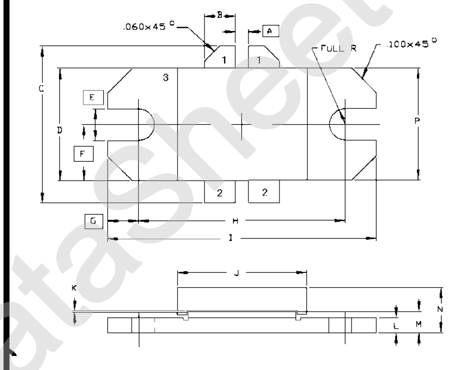
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	8.0 A
V_{CB}	45 V
P_{DISS}	155 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	1.15 °C/W

PACKAGE STYLE .450 BAL FLG.(A)



	MINIMUM Inches/mm	MAXIMUM Inches/mm
	.055/1,40	
B	.120/3,05	.130/3,30
C		.785/19,94
D	.455/11,56	.465/11,81
E	.130/3,30	
F	.230/5,84	
G	.128/3,25	
H	.838/21,28	.850/21,59
I	1.095/27,81	1.105/28,07
J	.525/13,34	.535/13,59

	MINIMUM Inches/mm	MAXIMUM Inches/mm
K	.002/0,05	.006/0,15
L	.055/1,40	.065/1,65
M	.080/2,03	.095/2,41
N		.195/4,95
P	.455/11,56	.468/11,89

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS (PER SIDE)	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 200 mA	30			V
BV_{CBO}	I_C = 50 mA	45			V
BV_{EBO}	I_E = 10 mA	3.0			V
h_{FE}	V_{CE} = 5.0 V I_C = 3.0 A	10		100	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz		72		pF
G_P	V_{CE} = 26.5 V I_C = 2 X 1.6 A f = 860 MHz	8.0	9.0		dB
G_p	V_{CE} = 28 V I_C = 2 X 250 mA f = 860 MHz P_{out} = 50 W	7.0	8.0		dB
IMD_3	V_{CE} = 26.5 V P_{out} = 25 W f = 860 MHz VISION = -8.0dB SOUND = -10 dB CHROMA = -16dB			-45	dBc